UNISONIC TECHNOLOGIES CO., LTD

UGP7N60

Preliminary

Insulated Gate Bipolar Transistor

600V, SMPS N-CHANNEL IGBT

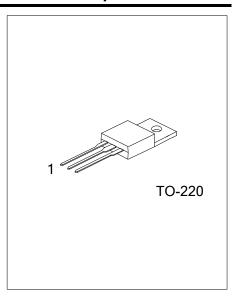
■ DESCRIPTION

The UTC **UGP7N60** is an N-channel IGBT. it uses UTC's advanced technology to provide customers with high input impedance, high switching speed and low conduction loss, etc.

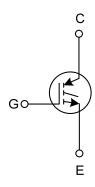
The UTC **UGP7N60** is suitable for high voltage switching, high frequency switch mode power supplies.

■ FEATURES

- * High switching speed
- * High input impedance
- * Low conduction loss

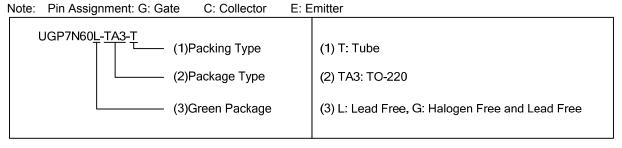


■ SYMBOL

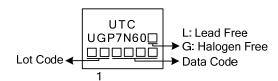


■ ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UGP7N60L-TA3-T	UGP7N60G-TA3-T	TO-220	G	С	Е	Tube	



■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage	V_{CES}	600	V	
Continuous Collector Current T _C =25°C	I _C	34	Α	
Continuous Collector Current T _C =110°C		14	Α	
Collector Current Pulsed (Note 2)	I _{CM}	56	Α	
Gate to Emitter Voltage Continuous	$V_{\sf GES}$	±20	V	
Gate to Emitter Voltage Pulsed	V_{GEM}	±30	V	
Switching Safe Operating Area at T _J =150°C	SSOA	35 (at 600V)	Α	
Single Pulse Avalanche Energy at T _C =25°C	E _{AS}	25 (at 7A)	mJ	
Power Dissipation Total at T _C =25°C	P_D	125	W	
Power Dissipation Derating T _C >25°C		1.0	W/°C	
Junction Temperature	T_J	-55~+150	°C	
Storage Temperature Range	T _{STG}	-55~+150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	$\theta_{ m JC}$	1.0	°C/W

■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C, unless otherwise specified)

SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
BV _{CES}	I _C =250μA, V _{GE} =0V		600			V
BV _{ECS}	I _C =10mA, V _{GE} =0V		20			V
I _{CES}	V _{CE} =600V	T _J =25°C			250	μΑ
		T _J =125°C			2	mA
	I _C =7A, V _{GE} =15V	T _J =25°C		1.3	2.7	V
VCE(SAT)		T _J =125°C		1	2.2	V
$V_{GE(TH)}$	I _C =250μA		4.5	5.9	7.2	V
I _{GES}	V _{GE} =±20V				±250	nA
8804	T _J =150°C, R _G =25Ω, V _{GE} =15V L=100μH, V _{GE} =600V		35			Α
330A			30			
E _{AS}	I _{CE} =7A, L=500μH		25			mJ
V_{GEP}	I _C =7A, V _{CE} =80V			10		V
	I _C =7A, V _{CE} =300V	V _{GE} =15V		37	45	nC
$Q_{g(ON)}$		V _{GE} =20V		48	60	nC
t _{dON)I}	IGBT and Diode at T_J =25°C, I_{CE} =7A, V_{GE} =13.5V, R_G =50Ω, R_L =1Ω, Test Circuit (Note)			400		ns
t _{rl}				2.6		μs
t _{dOFF)I}				300		ns
t _{fl}				2		μs
	BVCES BVECS ICES ICES VCE(SAT) VGE(TH) IGES SSOA EAS VGEP QG(ON) tdON)I tdOFF)I	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$				

Note: Pulse Test: Pulse width ≤ 50 µs.

^{2.} Pulse width limited by maximum junction temperature.

■ TEST CIRCUIT AND WAVEFORMS

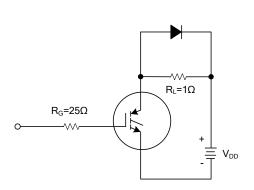


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

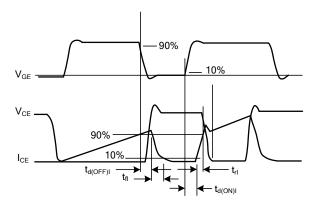


Fig 2. SWITCHING TEST WAVEFORMS

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